

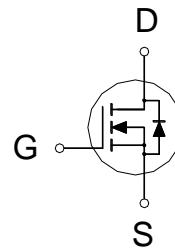
**NIKO-SEM****N-Channel Enhancement Mode  
Field Effect Transistor****PE8J6BA**

PDFN 3x3P

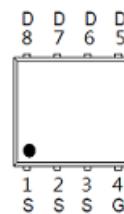
Halogen-Free &amp; Lead-Free

**PRODUCT SUMMARY**

$V_{(BR)DSS}$	$R_{DS(on)}$	$I_D$
40V	3.4mΩ	81A

**Features**

- Pb-Free, Halogen Free and RoHS compliant.
- Low  $R_{DS(on)}$  to Minimize Conduction Losses.
- Ohmic Region Good  $R_{DS(on)}$  Ratio.
- Optimized Gate Charge to Minimize Switching Losses.



G. GATE  
D. DRAIN  
S. SOURCE

100% UIS Tested  
100% Rg Tested

**Applications**

- Protection Circuits Applications.
- Computer for DC to DC Converters Applications.

**ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$  Unless Otherwise Noted)**

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		$V_{DS}$	40	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>4</sup>	$T_C = 25^\circ\text{C}$	$I_D$	81	A
	$T_C = 100^\circ\text{C}$		51	
Pulsed Drain Current <sup>1</sup>		$I_{DM}$	127	A
Continuous Drain Current	$T_A = 25^\circ\text{C}$	$I_D$	22	
	$T_A = 70^\circ\text{C}$		18	
Avalanche Current		$I_{AS}$	60	
Avalanche Energy	$L = 0.03\text{mH}$	$E_{AS}$	55	mJ
Power Dissipation	$T_C = 25^\circ\text{C}$	$P_D$	39	W
	$T_C = 100^\circ\text{C}$		16	
Power Dissipation <sup>3</sup>	$T_A = 25^\circ\text{C}$	$P_D$	3	W
	$T_A = 70^\circ\text{C}$		1.9	
Operating Junction & Storage Temperature Range		$T_j, T_{stg}$	-55 to 150	°C

**NIKO-SEM****N-Channel Enhancement Mode  
Field Effect Transistor****PE8J6BA**

PDFN 3x3P

Halogen-Free &amp; Lead-Free

**THERMAL RESISTANCE RATINGS**

THERMAL RESISTANCE		SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient <sup>2</sup>	$t \leq 10s$	$R_{\theta JA}$		42	°C / W
Junction-to-Ambient <sup>2</sup>	Steady-State	$R_{\theta JA}$		65	
Junction-to-Case	Steady-State	$R_{\theta JC}$		3.2	

<sup>1</sup>Pulse width limited by maximum junction temperature.<sup>2</sup>The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A = 25^\circ C$ .<sup>3</sup>The Power dissipation is based on  $R_{\theta JA} t \leq 10s$  value.<sup>4</sup>The maximum current rating is package limited.**ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ C$ , Unless Otherwise Noted)**

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
<b>STATIC</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	40			
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.3	1.6	2.3	V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0V, V_{GS} = \pm 20V$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 40V, V_{GS} = 0V$			1	$\mu A$
		$V_{DS} = 40V, V_{GS} = 0V, T_J = 55^\circ C$			10	
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = 4.5V, I_D = 20A$		3.3	4.6	$m\Omega$
		$V_{GS} = 10V, I_D = 20A$		2.5	3.4	
Forward Transconductance	$g_{fs}$	$V_{DS} = 5V, I_D = 20A$		107		S
<b>DYNAMIC</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0V, V_{DS} = 20V, f = 700kHz$		2136		pF
Output Capacitance	$C_{oss}$			552		
Reverse Transfer Capacitance	$C_{rss}$			12.2		
Gate Resistance	$R_g$	$f = 1MHz$		1.6		$\Omega$
Total Gate Charge <sup>5</sup>	$Q_g$	$V_{GS} = 10V$ $V_{GS} = 4.5V$ $V_{DS} = 20V, V_{GS} = 10V, I_D = 20A$		30		nC
				13		
Gate-Source Charge <sup>5</sup>	$Q_{gs}$			6.9		
Gate-Drain Charge <sup>5</sup>	$Q_{gd}$			2.1		
Turn-On Delay Time <sup>5</sup>	$t_{d(on)}$			11		
Rise Time <sup>5</sup>	$t_r$			63		
Turn-Off Delay Time <sup>5</sup>	$t_{d(off)}$	$V_{DS} = 20V, I_D \approx 20A, V_{GS} = 10V, R_{GEN} = 6\Omega$		37		nS
Fall Time <sup>5</sup>	$t_f$			103		

**NIKO-SEM****N-Channel Enhancement Mode  
Field Effect Transistor****PE8J6BA**

PDFN 3x3P

Halogen-Free &amp; Lead-Free

**SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T<sub>J</sub> = 25 °C)**

Continuous Current <sup>6</sup>	I <sub>S</sub>				33	A
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = 20A, V <sub>GS</sub> = 0V			1.2	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 20A, dI <sub>F</sub> /dt = 400A / μS		21		nS
Reverse Recovery Charge	Q <sub>rr</sub>			41		nC

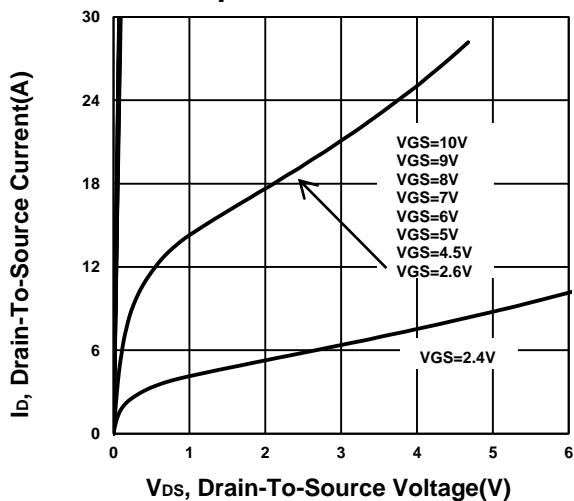
<sup>5</sup>Independent of operating temperature.<sup>6</sup>The maximum current rating is package limited.

**NIKO-SEM**

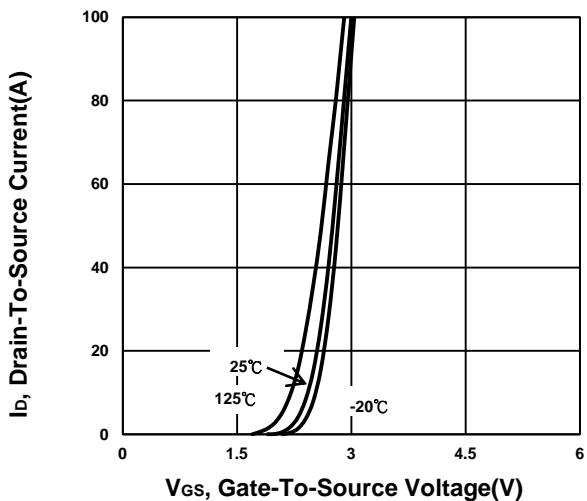
**N-Channel Enhancement Mode  
Field Effect Transistor**

**PE8J6BA**  
**PDFN 3x3P**  
**Halogen-Free & Lead-Free**

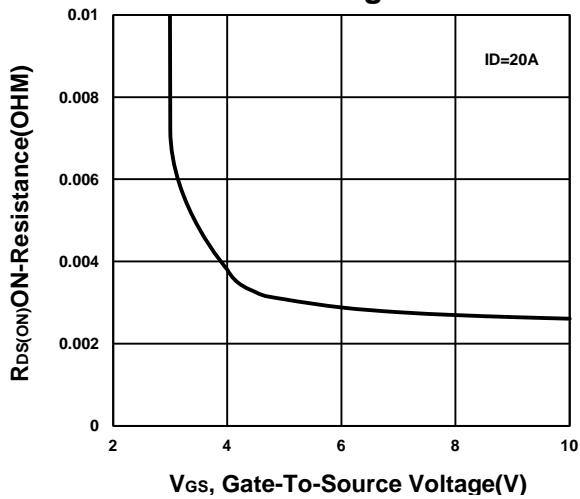
**Output Characteristics**



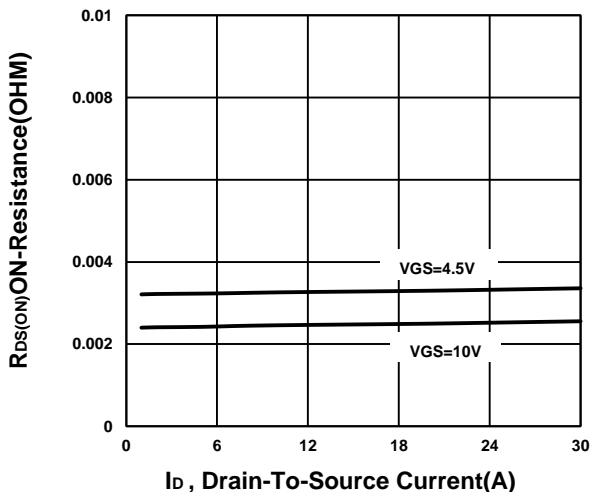
**Transfer Characteristics**



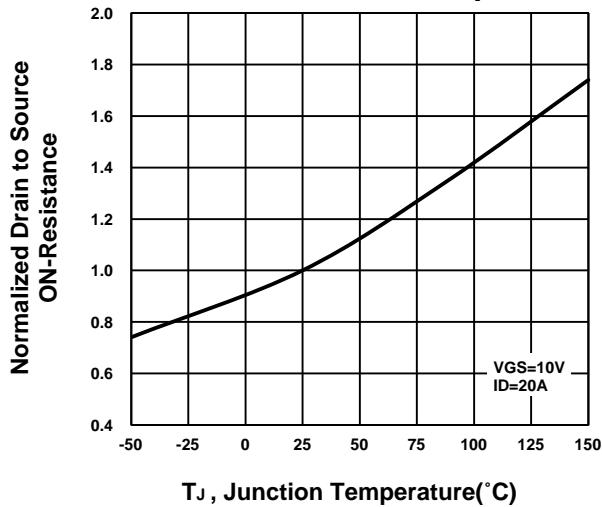
**On-Resistance VS Gate-To-Source Voltage**



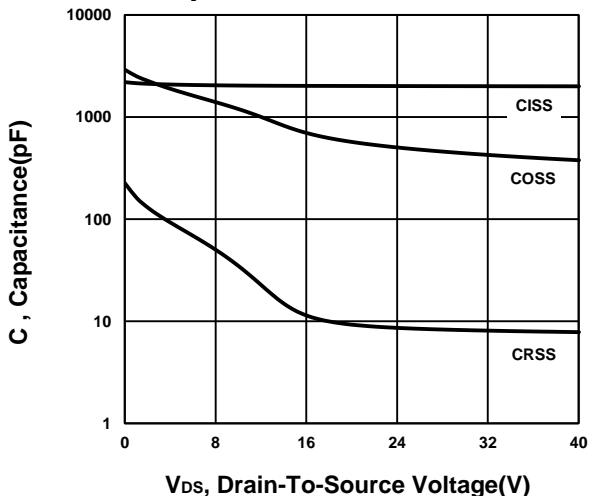
**On-Resistance VS Drain Current**



**On-Resistance VS Temperature**



**Capacitance Characteristic**



**NIKO-SEM****N-Channel Enhancement Mode  
Field Effect Transistor****PE8J6BA  
PDFN 3x3P  
Halogen-Free & Lead-Free**